Surface roughness in XeF₂ etching of a-Si/c-Si(100). [Erratum to document cited in CA143:121009]

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Erratum: “Surface roughness in XeF_2 etching of $a\text{-Si}/c\text{-Si}(100)$ [J. Vac. Sci. Technol. A 23, 126 (2005)]”*

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Figure 16 in the publication was incorrectly submitted. The correct figure is:

FIG. 16. Surface area increase ρ , $\text{SiF}_{1.2}$ and SiF_3 surface coverage (in ML) and SiF_4 production coefficient $\delta_{\text{calculated}}$ resulting from the bilayer model, as well as the measured δ_{measured} , as a function of XeF_2 . For a XeF_2 dose less than 10^3 ML, ρ is equal to 1 and the SiF_x coverages follow from matching $\delta_{\text{calculated}}$ with δ_{measured} by determining the back bond breaking probability k_b and etching probability k_e . For XeF_2 dose above 10^3 ML, the increase ρ in surface area is the only variable used to match $\delta_{\text{calculated}}$ with δ_{measured} .

*No proof corrections received from author prior to publication.

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